

AMENDMENT TO THE CLAIMS

IN THE CLAIMS:

Please **AMEND** claims 3, 5, 6, 7, 8, 15 and 16; and

Please **ADD** claim 27 as follows.

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Original) A device, comprising:
an active region including a collector region;
an oxide layer formed over the collector region and having a conductive pathway in electrical contact with the collector region; and
a collector metal contact deposited over the oxide layer and the conductive pathway;
wherein the conductive pathway through the oxide layer provides electrical contact between the collector metal contact and the collector region.
2. (Original) The structure of claim 1, wherein the active region includes an emitter region, a base region deposited on a top surface of the emitter region, and the collector region deposited on a top surface of the base region.
3. (Currently Amended) The structure of claim ~~[[1]]~~ 2, further comprising a passivation layer deposited about the emitter region and about the base region, and a second oxide layer deposited around a side of the collector region and in contact with the oxide layer.

4. (Original) The structure of claim 1, wherein the conductive pathway through the oxide layer from the collector metal contact to the collector region comprises a vertical conductive pathway.

5. (Currently Amended) The structure of claim 1, wherein the conductive pathway through the oxide layer from the collector metal contact to the collector region comprises of a metal filled via.

6. (Currently Amended) The structure of claim 1, further comprising a silicide layer disposed between the a surface of the collector region and the oxide layer.

7. (Currently Amended) The structure of claim 1, wherein the conductive pathway to the collector region comprises a base metal contact disposed on the a top of the oxide layer.

8. (Currently Amended) The structure of claim 7, further comprising a further conductive pathway to at least one of the a base region and the emitter region.

9. (Withdrawn) The structure of claim 8, wherein the further conductive pathway includes a first conductive pathway and a second conductive pathway, wherein the first conductive pathway comprises filled vias formed in the oxide layer, the second oxide layer and the passivation layer and between metal contacts and the emitter region, wherein the second conductive pathway includes a filled via formed in the oxide layer and the second oxide layer and between a metal contact and the base region.

10. (Withdrawn) The structure of claim 8, wherein the first conductive pathway is formed in the oxide layer, the second oxide and the passivation layer.

11. (Withdrawn) The structure of claim 10, wherein the first conductive pathway includes filled vias formed in the oxide layer and the second oxide layer and the passivation layer, and between metal contacts and the emitter region, wherein the second conductive pathway includes a filled via formed in the oxide layer and the second oxide layer and between a metal contact and the base region.

12. (Withdrawn) The structure of claim 10, wherein the second conductive pathway includes filled vias disposed within the oxide layer and the second oxide layer between a base metal contact and the base region and the emitter region.

13. (Original) A semiconductor device, comprising:
an emitter region;
a base region laying on a surface of the emitter region;
a passivation layer deposited about the emitter region and about an edge of the base region;
a collector region laying on the base region and electrically isolated from a substrate; and
an oxide layer deposited about at least one side and on a surface of the collector region.

14. (Original) The semiconductor device of claim 13, further comprising:
a conductive pathway to the collector region within a portion of the oxide layer formed on top of the collector region; and

a metal contact formed on the oxide layer and the conductive pathway to provide electrical contact to the collector region.

15. (Currently Amended) The semiconductor device of claim ~~[[14]]~~ 13, further comprising a conductive pathway to the base region through the passivation layer.

16. (Currently Amended) The semiconductor device of claim 15, wherein the conductive pathway to the base region comprises a base metal contact on a top of the oxide layer and a filled via through the oxide layer between a base metal contact and ~~the~~ a extrinsic base region.

17. (Withdrawn) The semiconductor device of claim 13, further comprising a conductive pathway to the emitter region including a conductive pathway through the oxide layer and the passivation layer.

18. (Original) The semiconductor device of claim 13, wherein the oxide layer comprises a first oxide layer deposited about at least one side of the collector region and a second oxide layer deposited on a top surface of the collector region.

Claims 19-26 (Canceled).

27. (New) The semiconductor device of claim 13, wherein the surface of the collector region which is deposited with the oxide layer is opposite a side of the collector region that faces the emitter region.